



**Advanced Power
Electronics Corp.**

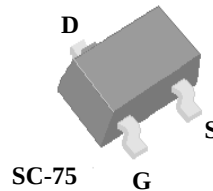
AP1332GEV-HF

Halogen-Free Product

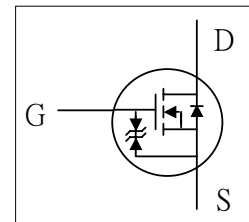
N-CHANNEL ENHANCEMENT MODE

POWER MOSFET

- ▼ Lower Gate Charge
- ▼ Gate Pateded Diode
- ▼ Small Package Outline
- ▼ RoHS Compliant & Halogen-Free



BV_{DSS}	20V
$R_{DS(ON)}$	0.9Ω
I_D	450mA



Description

Advanced Power MOSFETs from APEC provide the designer with the best combination of fast switching, low on-resistance and cost-effectiveness.

SC-75 with 1.6x1.6mm very small footprint and suited for hand held applications.

Absolute Maximum Ratings

Symbol	Parameter	Rating	Unit
V_{DS}	Drain-Source Voltage	20	V
V_{GS}	Gate-Source Voltage	± 6	V
$I_D @ T_A = 25^\circ\text{C}$	Continuous Drain Current ³	450	mA
$I_D @ T_A = 70^\circ\text{C}$	Continuous Drain Current ³	360	mA
I_{DM}	Pulsed Drain Current ¹	1	A
$P_D @ T_A = 25^\circ\text{C}$	Total Power Dissipation	0.35	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Value	Unit
Rthj-a	Maximum Thermal Resistance, Junction-ambient ³	420	$^\circ\text{C/W}$

Data and specifications subject to change without notice

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Electrical Characteristics@T_J=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	20	-	-	V
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =4.5V, I _D =400mA	-	-	0.9	Ω
		V _{GS} =2.5V, I _D =300mA	-	-	1	Ω
		V _{GS} =1.8V, I _D =200mA	-	-	1.5	Ω
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250uA	0.25	-	1	V
g _{fs}	Forward Transconductance	V _{DS} =5V, I _D =400mA	-	1.3	-	S
I _{DSS}	Drain-Source Leakage Current	V _{DS} =16V, V _{GS} =0V	-	-	10	uA
I _{GSS}	Gate-Source Leakage	V _{GS} =±6V, V _{DS} =0V	-	-	±30	uA
Q _g	Total Gate Charge	I _D =400mA	-	1.2	1.9	nC
Q _{gs}	Gate-Source Charge	V _{DS} =10V	-	0.3	-	nC
Q _{gd}	Gate-Drain ("Miller") Charge	V _{GS} =4.5V	-	0.3	-	nC
t _{d(on)}	Turn-on Delay Time	V _{DS} =10V	-	18	-	ns
t _r	Rise Time	I _D =400mA	-	34	-	ns
t _{d(off)}	Turn-off Delay Time	R _G =3.3Ω	-	110	-	ns
t _f	Fall Time	V _{GS} =5V	-	115	-	ns
C _{iss}	Input Capacitance	V _{GS} =0V	-	45	72	pF
C _{oss}	Output Capacitance	V _{DS} =10V	-	22	-	pF
C _{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	12	-	pF

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{SD}	Forward On Voltage ²	I _S =300mA, V _{GS} =0V	-	-	1.2	V

Notes:

- 1.Pulse width limited by Max. junction temperature.
- 2.Pulse test.
- 3.Surface mounted on FR4 board.

THIS PRODUCT IS SENSITIVE TO ELECTROSTATIC DISCHARGE, PLEASE HANDLE WITH CAUTION.

USE OF THIS PRODUCT AS A CRITICAL COMPONENT IN LIFE SUPPORT OR OTHER SIMILAR SYSTEMS IS NOT AUTHORIZED.

APEC DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

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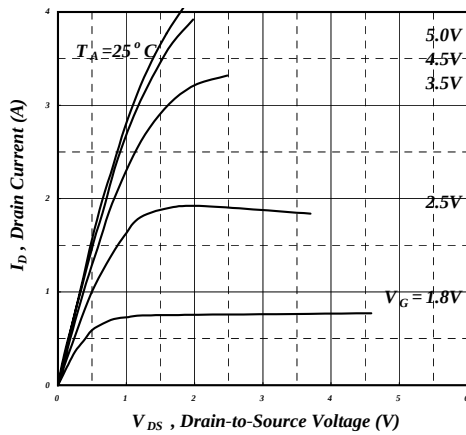


Fig 1. Typical Output Characteristics

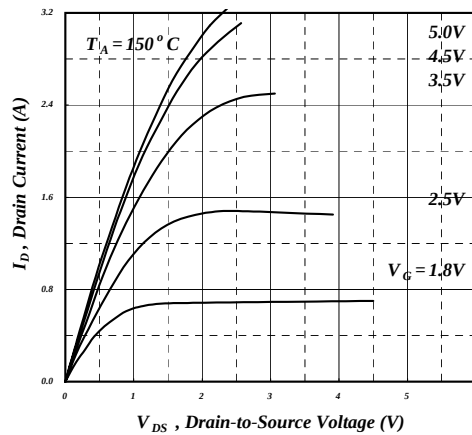


Fig 2. Typical Output Characteristics

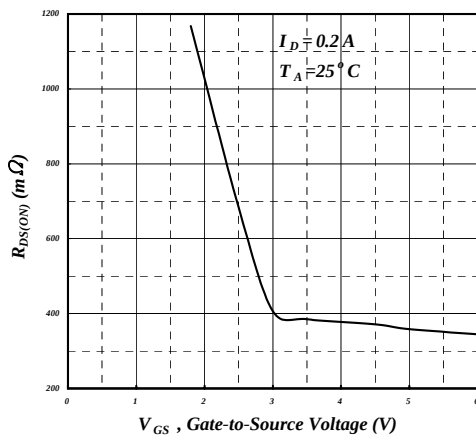


Fig 3. On-Resistance v.s. Gate Voltage

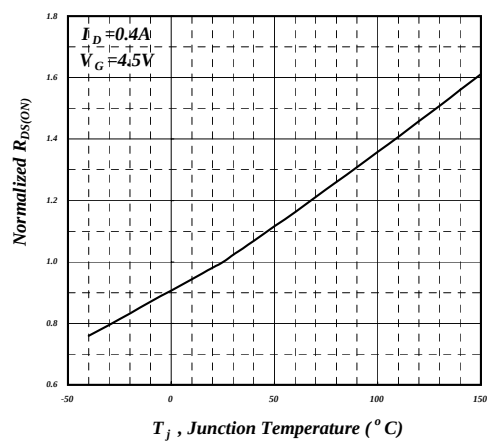


Fig 4. Normalized On-Resistance v.s. Junction Temperature

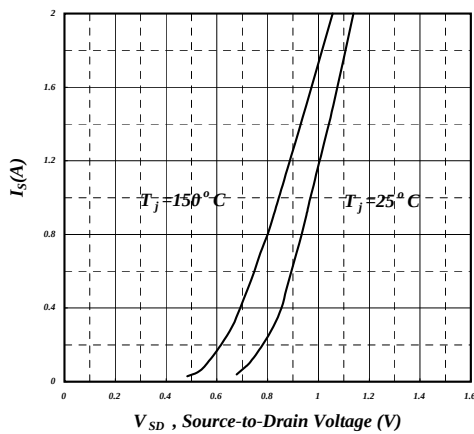


Fig 5. Forward Characteristic of Reverse Diode

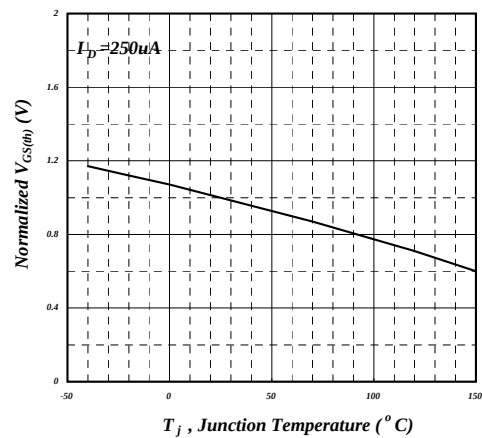


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

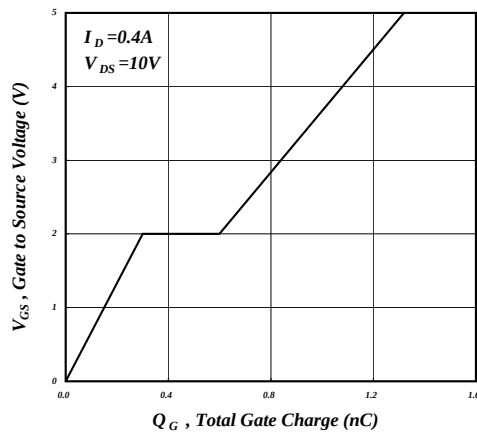


Fig 7. Gate Charge Characteristics

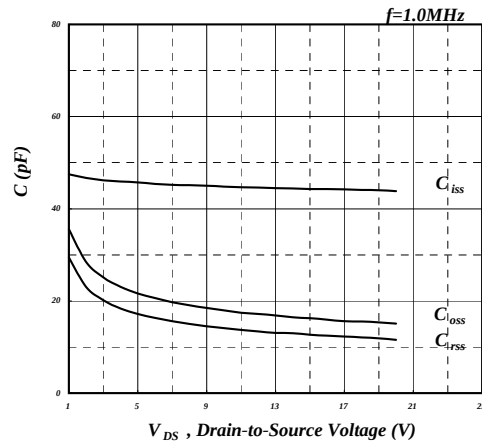


Fig 8. Typical Capacitance Characteristics

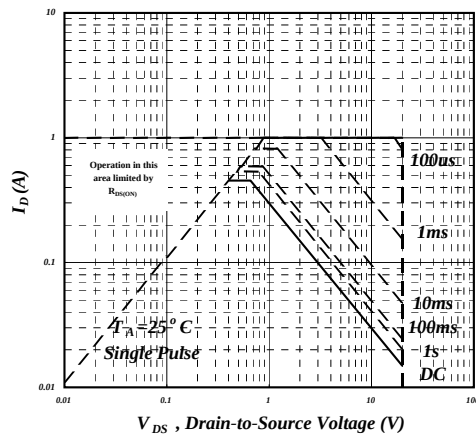


Fig 9. Maximum Safe Operating Area

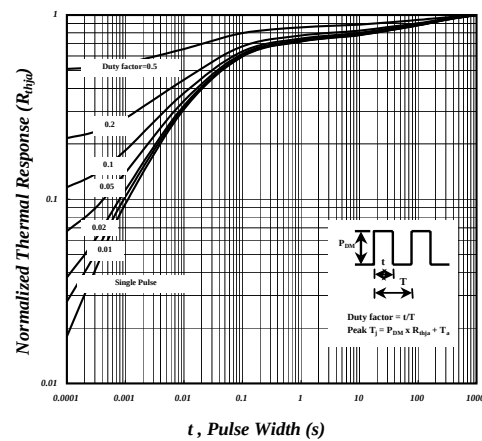


Fig 10. Effective Transient Thermal Impedance

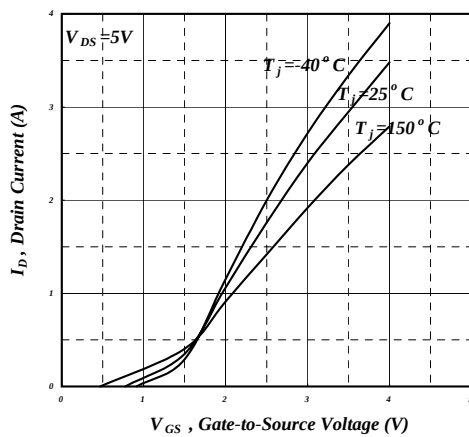


Fig 11. Transfer Characteristics

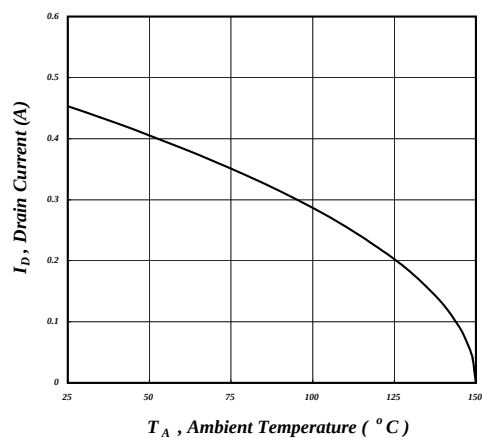


Fig 12. Maximum Continuous Drain Current
v.s. Ambient Temperature